



	°C			



	°C					
	°C					
	°C					
	°C					
	°C					
	°C					
	°C					



FIG.1: Power dissipation vs. on-state current
(per thyristor or diode)

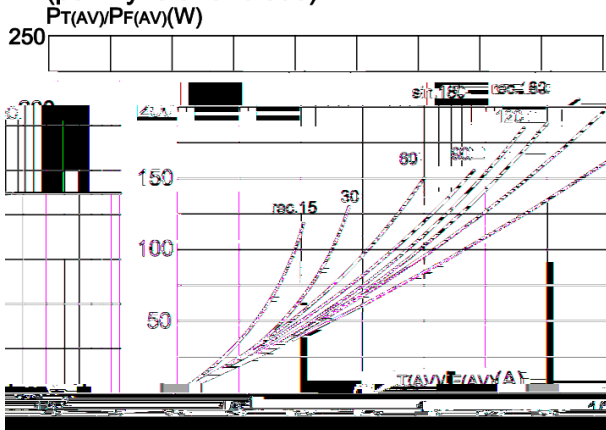


FIG.2: Maximum transient thermal impedance
junction to case(per thyristor or diode)

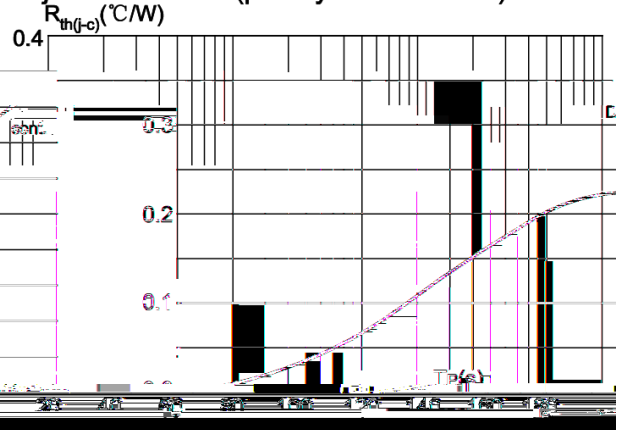


FIG.3: Forward characteristics
(per thyristor or diode)

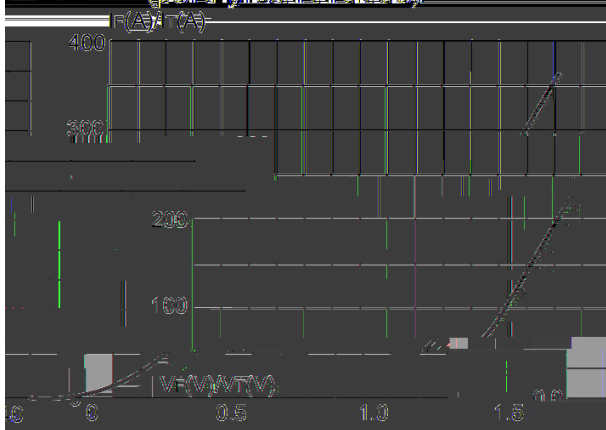


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

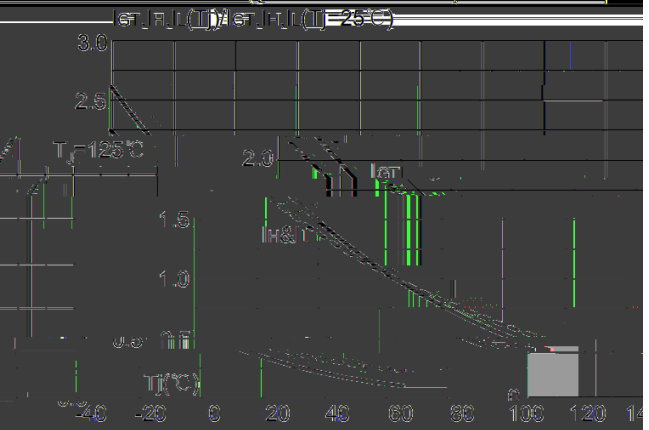


FIG.5: Gate trigger characteristics

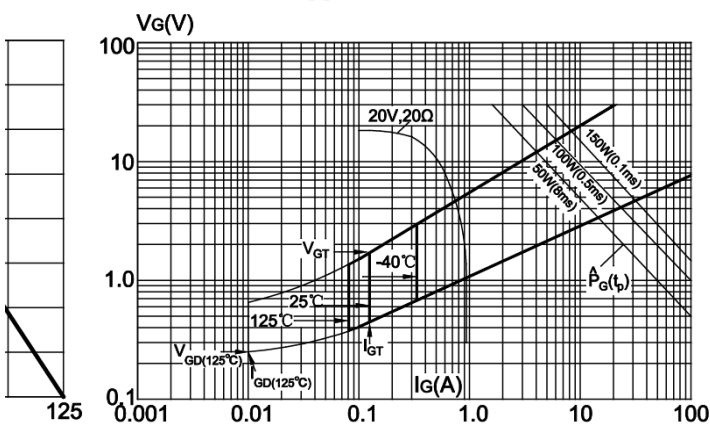


FIG.6: Forward current vs. case temperature
(per thyristor or diode)

